

Description

The TFD085N03M uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other switching application.

General Feature

$V_{DS} = 30V$, $I_D = 25A$

$R_{DS(ON) Typ} = 8.5m\Omega @ V_{GS}=10V$

$R_{DS(ON) Typ} = 10m\Omega @ V_{GS}=4.5V$

High Power and current handling capability

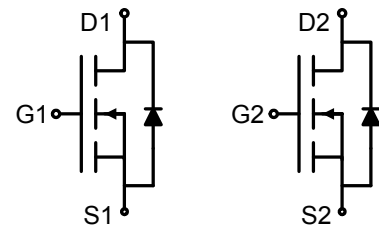
Lead free product is acquired

Surface mount package

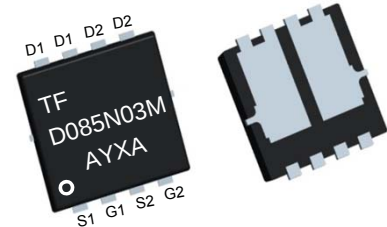
Application

Battery switch

DC/DC converter



Schematic diagram



PDFN3333-8

●Package Marking and Ordering Information:

Part NO.	TFD085N03M
Marking1	D085N03M: TFD085N03M
Marking2	TF:tuofeng; Y:year code; X:Week; AA:device code;
Basic ordering unit (pcs)	5000

●Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	25	A
	$I_{D@TC=75^\circ C}$	17	A
	$I_{D@TC=100^\circ C}$	12	A
Pulsed Drain Current ①	I_{DM}	75	A
Total Power Dissipation	$P_{D@TC=25^\circ C}$	16	W
Total Power Dissipation	$P_{D@TA=25^\circ C}$	0.9	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	56	mJ

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	8.0	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	55	° C/W
Soldering temperature, wavesoldering for 8 s	T_{sold}	-	-	265	° C

●Electronic Characteristics($T_j=25$,unless otherwise notse)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.1	1.5	1.9	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=15A$	-	8.5	10	m Ω
		$V_{GS}=4.5V, I_D=10A$	-	10	13	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=10A$	-	10	-	S
Source-drain voltage	V_{SD}	$I_S=10A$	-	-	1.20	V

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz $V_{DS}=15V$ $V_{GS}=0V$	-	927.2	-	pF
Output capacitance	C_{oss}		-	141.1	-	
Reverse transfer capacitance	C_{rss}		-	126.9	-	

●Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 24V$	-	23.0	-	nC
Gate - Source charge	Q_{gs}	$I_D = 10A$	-	2.58	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	6.20	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Typical Electrical and Thermal Characteristics

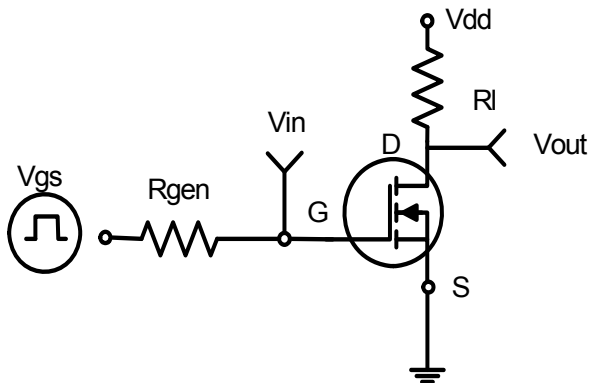


Figure 1 Switching Test Circuit

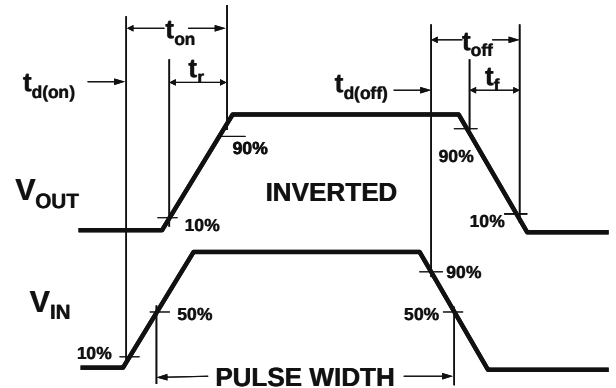


Figure 2 Switching Waveforms

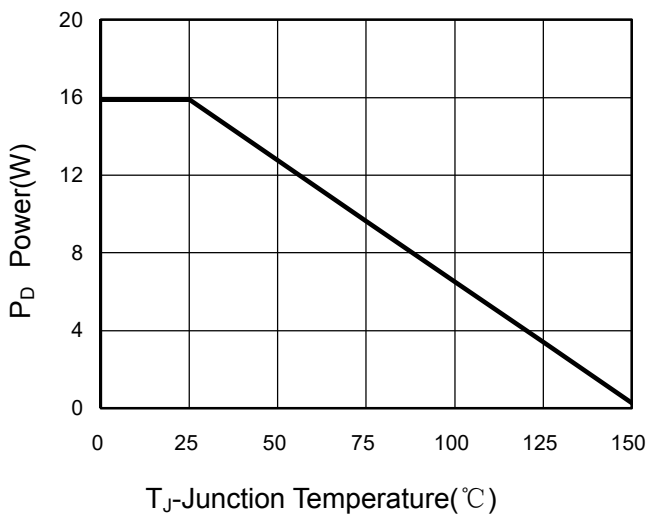


Figure 3 Power Dissipation

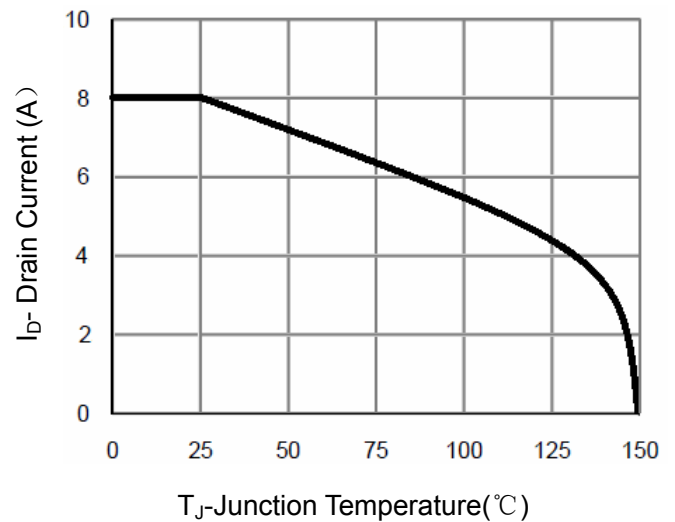


Figure 4 Drain Current

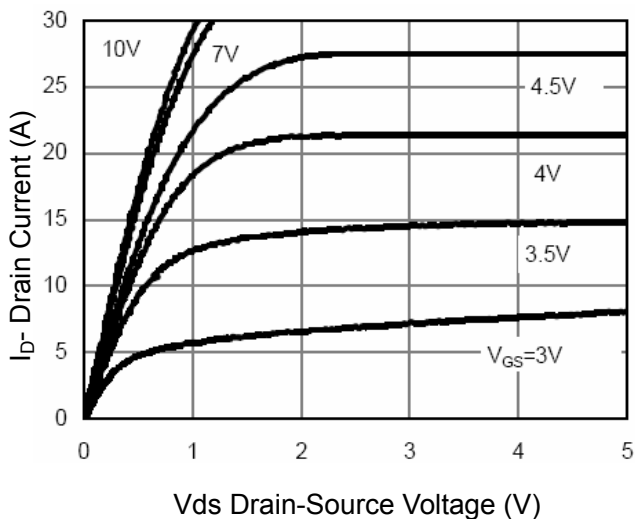


Figure 5 Output Characteristics

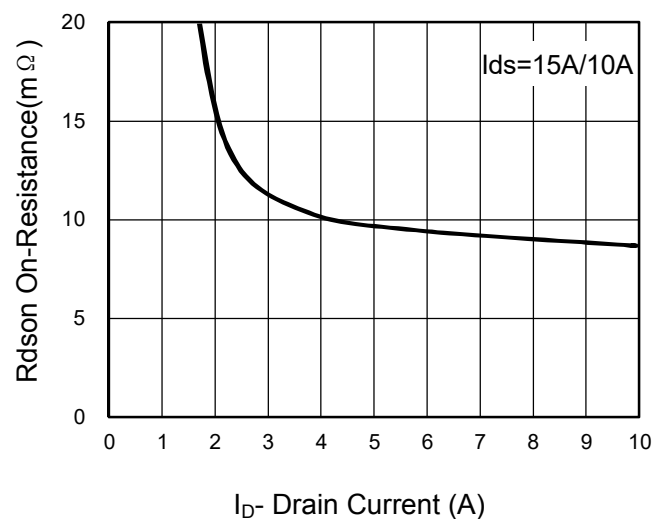


Figure 6 Drain-Source On-Resistance

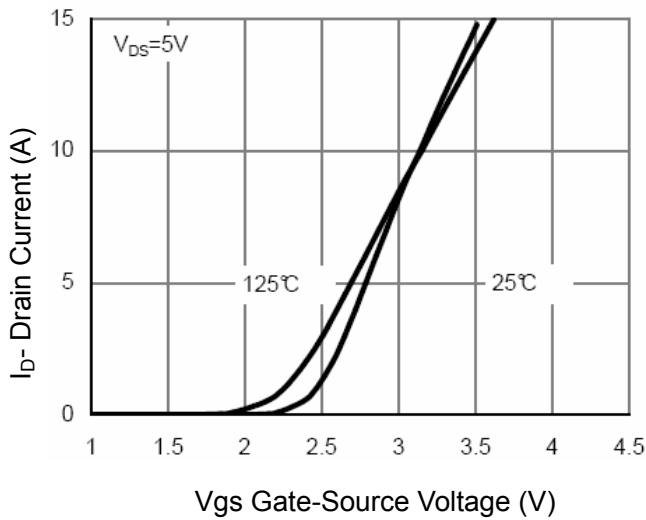


Figure 7 Transfer Characteristics

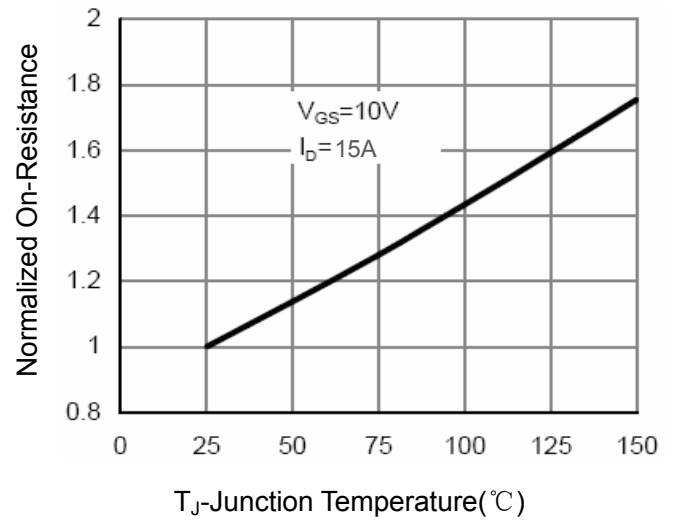


Figure 8 Drain-Source On-Resistance

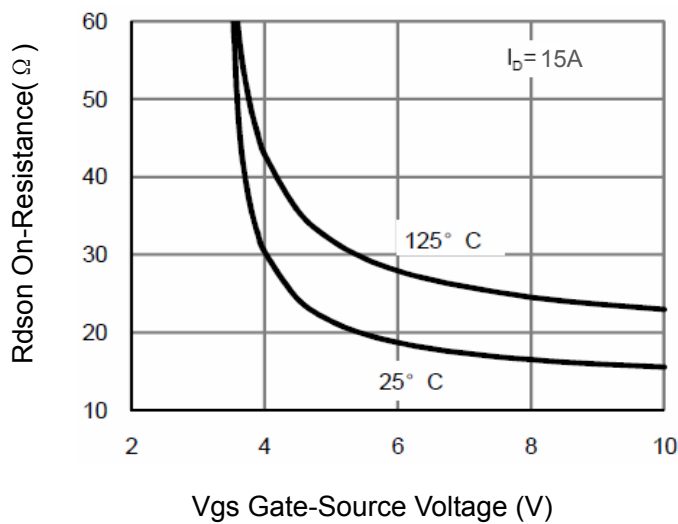


Figure 9 Rdson vs Vgs

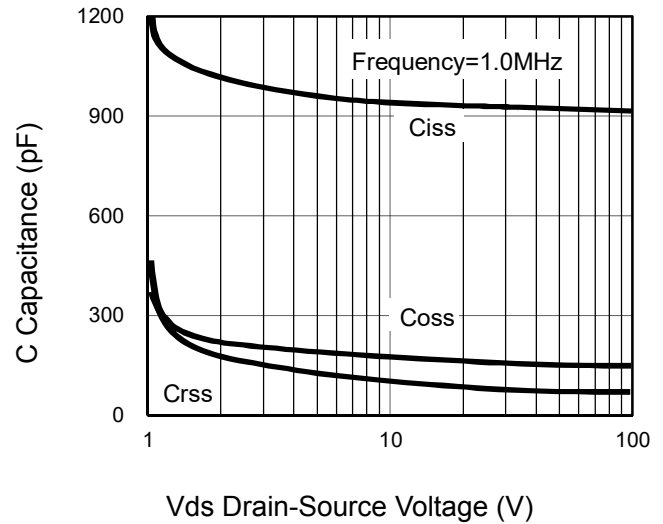


Figure 10 Capacitance vs Vds

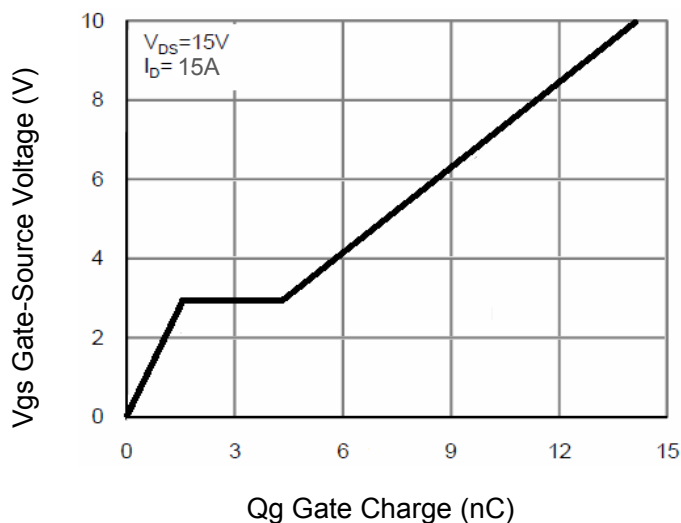


Figure 11 Gate Charge

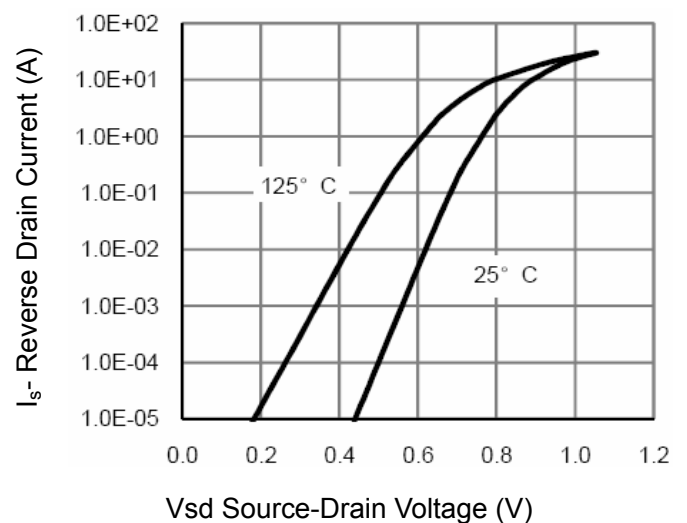


Figure 12 Source- Drain Diode Forward

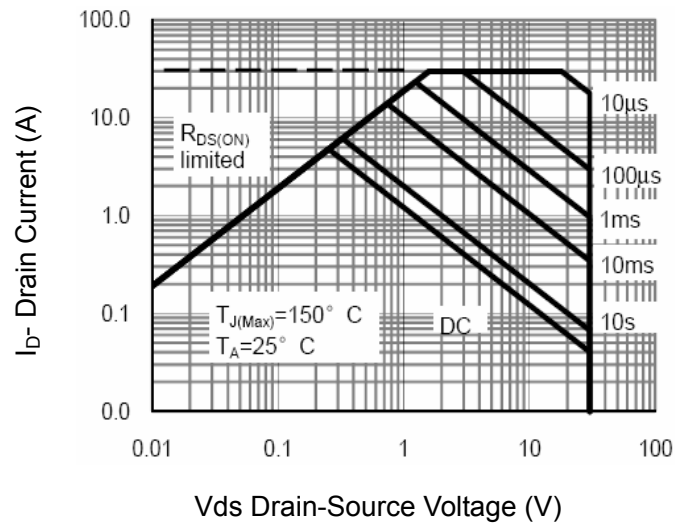


Figure 13 Safe Operation Area

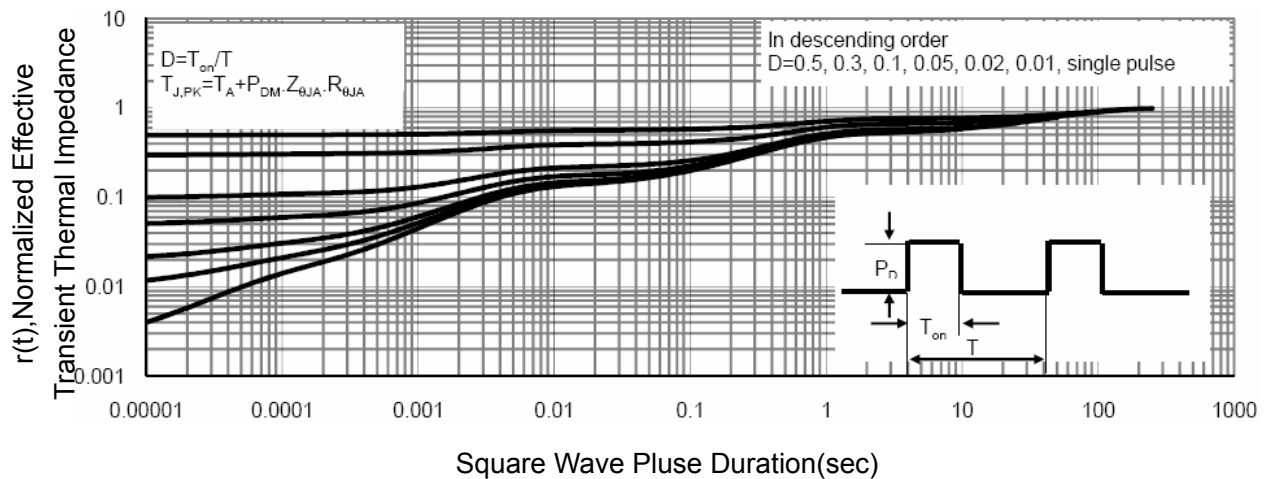
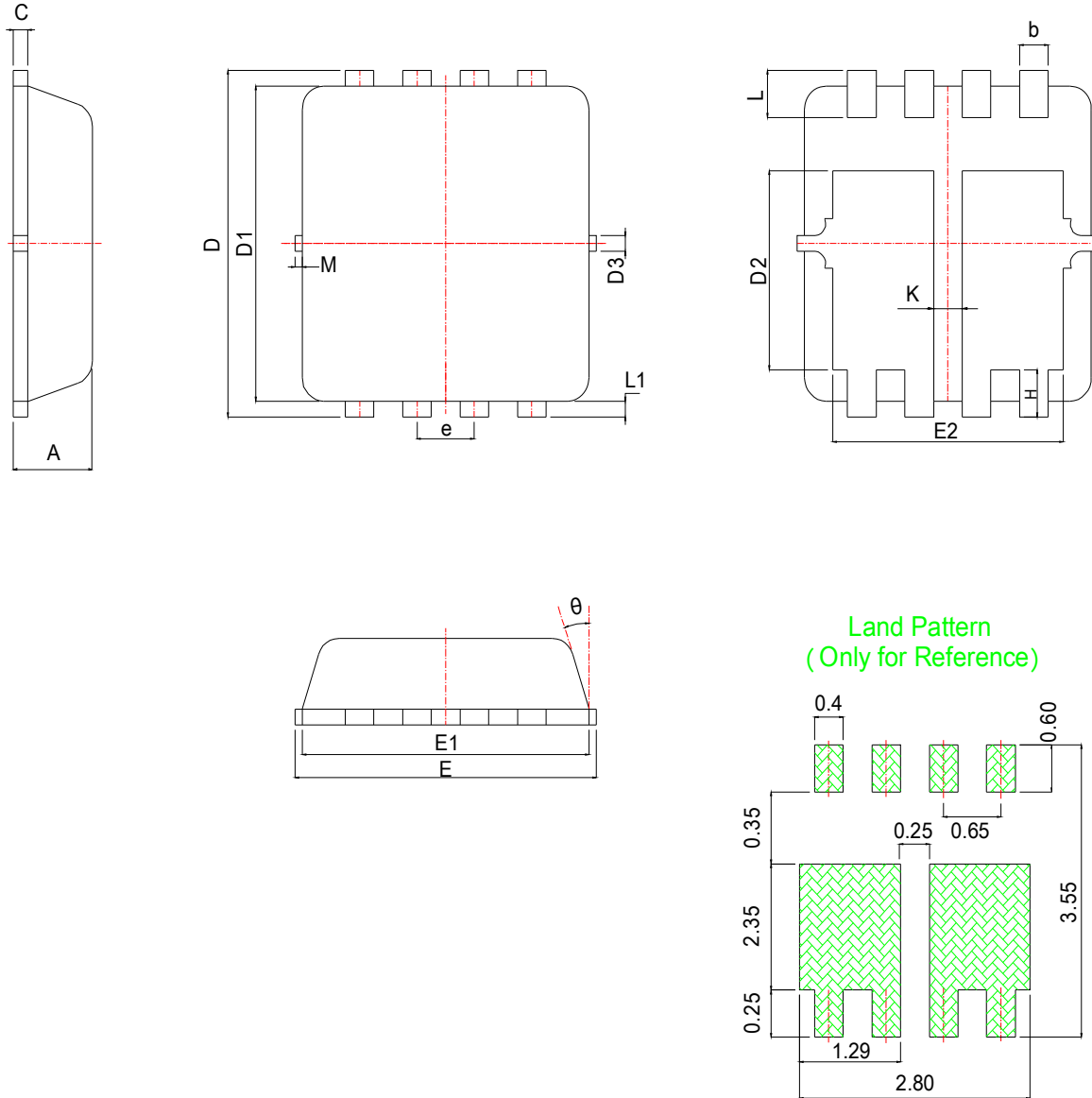


Figure 14 Normalized Maximum Transient Thermal Impedance

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SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031	E1	3.00	3.15	3.20	0.118	0.122	0.126
b	0.25	0.30	0.35	0.010	0.012	0.014	E2	2.39	2.49	2.59	0.094	0.098	0.102
c	0.10	0.15	0.25	0.004	0.007	0.010	e	0.65BSC			0.026BSC		
D	3.25	3.35	3.45	0.128	0.132	0.136	H	0.30	0.40	0.50	0.012	0.016	0.020
D1	3.00	3.10	3.20	0.118	0.122	0.126	L	0.30	0.40	0.50	0.012	0.016	0.020
D2	1.78	1.88	1.98	0.070	0.074	0.078	L1	*	0.13	*	*	0.005	*
D3	*	0.13	*	*	0.005	*	θ	*	10°	12°	*	10°	12°
E	3.20	3.30	3.40	0.126	0.130	0.134	M	*	*	0.15	*	*	0.006
K	0.30	*	*	0.012	*	*							